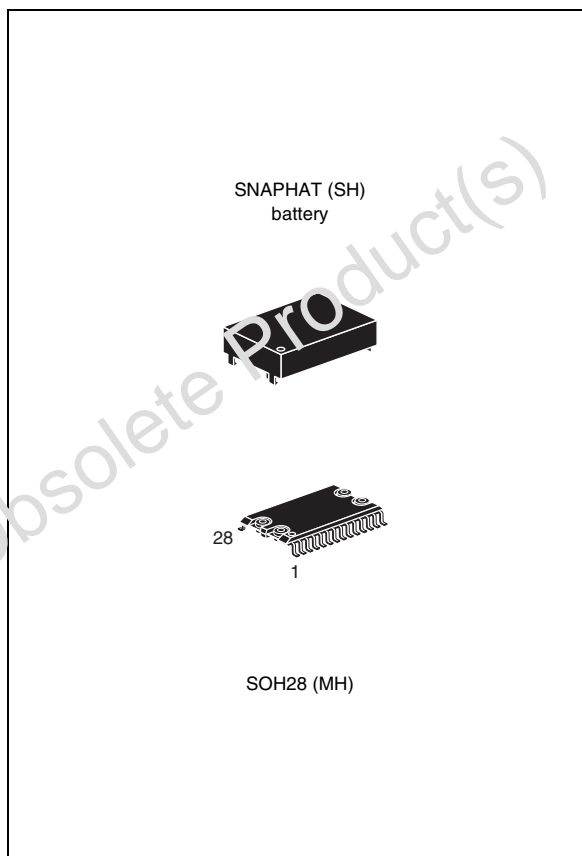


5 V or 3 V NVRAM supervisor for up to two LPSRAMs

Not recommended for new design

Features

- Convert low power SRAMs into NVRAMs
- Precision power monitoring and power switching circuitry
- Automatic write-protection when V_{CC} is out-of-tolerance
- Choice of supply voltages and power-fail deselect voltages:
 - M40Z111: $V_{CC} = 4.5$ to 5.5 V
THS = V_{SS} ; $4.5 \leq V_{PFD} \leq 4.75$ V
THS = V_{OUT} ; $4.2 \leq V_{PFD} \leq 4.5$ V
 - M40Z111W: $V_{CC} = 3.0$ to 3.6 V
THS = V_{SS} ; $2.8 \leq V_{PFD} \leq 3.0$ V
 $V_{CC} = 2.7$ to 3.3 V
THS = V_{OUT} ; $2.5 \leq V_{PFD} \leq 2.7$ V
- Less than 15 ns chip enable access propagation delay (for 5.0 V device)
- Packaging includes a 28-lead SOIC and SNAPHAT[®] top (to be ordered separately)
- SOIC package provides direct connection for a SNAPHAT top which contains the battery
- RoHS compliant
 - Lead-free second level interconnect



Contents

| | | |
|----------|--|-----------|
| 1 | Description | 5 |
| 2 | Operation | 8 |
| | 2.1 Data retention lifetime calculation | 8 |
| | 2.2 V_{CC} noise and negative going transients | 10 |
| 3 | Maximum ratings | 11 |
| 4 | DC and AC parameters | 12 |
| 5 | Package mechanical data | 14 |
| 6 | Part numbering | 18 |
| 7 | Revision history | 19 |

Obsolete Product(s) - Obsolete Product(s)

List of tables

| | | |
|-----------|--|----|
| Table 1. | Signal names | 6 |
| Table 2. | Power down/up AC characteristics | 10 |
| Table 3. | Absolute maximum ratings | 11 |
| Table 4. | DC and AC measurement conditions | 12 |
| Table 5. | Capacitance | 12 |
| Table 6. | DC characteristics | 13 |
| Table 7. | SOH28 – 28-lead plastic small outline, battery SNAPHAT, pack. mech. data | 15 |
| Table 8. | 4-pin SNAPHAT housing for 48 mAh battery, package mechanical data | 16 |
| Table 9. | 4-pin SNAPHAT housing for 120 mAh battery, package mechanical data | 17 |
| Table 10. | Ordering information scheme | 18 |
| Table 11. | Battery table | 18 |
| Table 12. | Document revision history | 19 |

List of figures

| | | |
|------------|--|----|
| Figure 1. | Logic diagram | 5 |
| Figure 2. | SOIC28 connections | 6 |
| Figure 3. | Hardware hookup | 7 |
| Figure 4. | Power-down timing | 9 |
| Figure 5. | Power-up timing | 9 |
| Figure 6. | Supply voltage protection | 10 |
| Figure 7. | AC testing load circuit | 12 |
| Figure 8. | SOH28 – 28-lead plastic small outline, 4-socket battery SNAPHAT, package outline | 15 |
| Figure 9. | 4-pin SNAPHAT housing for 48 mAh battery, package outline | 16 |
| Figure 10. | 4-pin SNAPHAT housing for 120 mAh battery, package outline | 17 |

Obsolete Product(s) - Obsolete Product(s)

1 Description

The M40Z111/W NVRAM supervisor is a self-contained device which converts a standard low-power SRAM into a non-volatile memory.

A precision voltage reference and comparator monitors the V_{CC} input for an out-of-tolerance condition.

When an invalid V_{CC} condition occurs, the conditioned chip enable (\bar{E}_{CON}) output is forced inactive to write-protect the stored data in the SRAM.

During a power failure, the SRAM is switched from the V_{CC} pin to the lithium cell within the SNAPHAT[®] to provide the energy required for data retention. On a subsequent power-up, the SRAM remains write protected until a valid power condition returns.

The 28-pin, 330 mil SOIC provides sockets with gold plated contacts at both ends for direct connection to a separate SNAPHAT housing containing the battery. The unique design allows the SNAPHAT battery package to be mounted on top of the SOIC package after the completion of the surface mount process.

Insertion of the SNAPHAT housing after reflow prevents potential battery damage due to the high temperatures required for device surface-mounting. The SNAPHAT housing is keyed to prevent reverse insertion.

The SOIC and battery packages are shipped separately in plastic anti-static tubes or in tape & reel form. For the 28-lead SOIC, the battery package (e.g., SNAPHAT) part number is "M4Z28-BR00SH1" (SNAPHAT housing for 48 mAh battery) or "M4Z32-BR00SH1" (SNAPHAT housing for 120 mAh battery).

Figure 1. Logic diagram

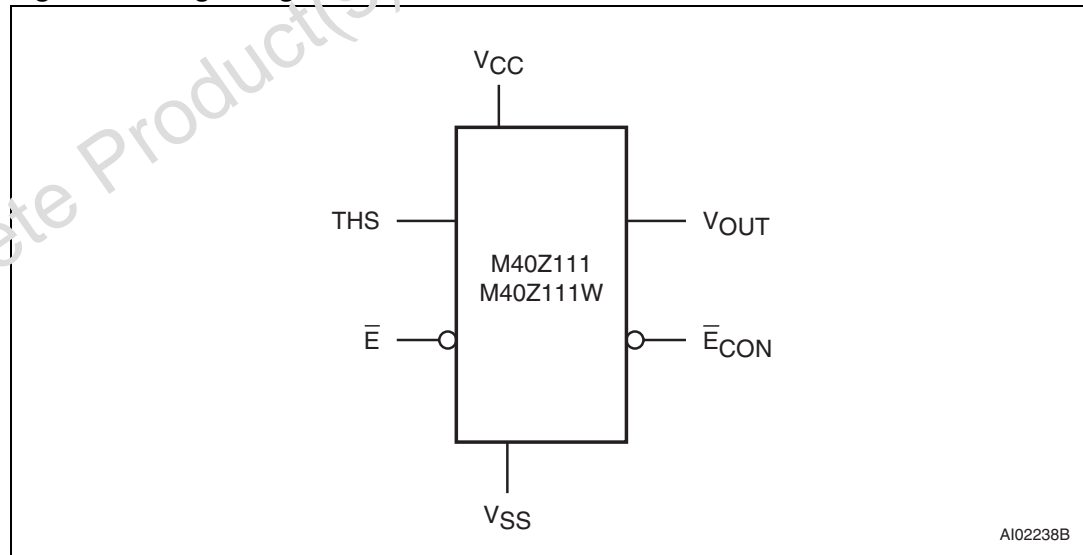


Table 1. Signal names

| | |
|-----------------|--------------------------------|
| THS | Threshold select input |
| \bar{E} | Chip enable input |
| \bar{E}_{CON} | Conditioned chip enable output |
| V_{OUT} | Supply voltage output |
| V_{CC} | Supply voltage |
| V_{SS} | Ground |
| NC | Not connected internally |

Figure 2. SOIC28 connections

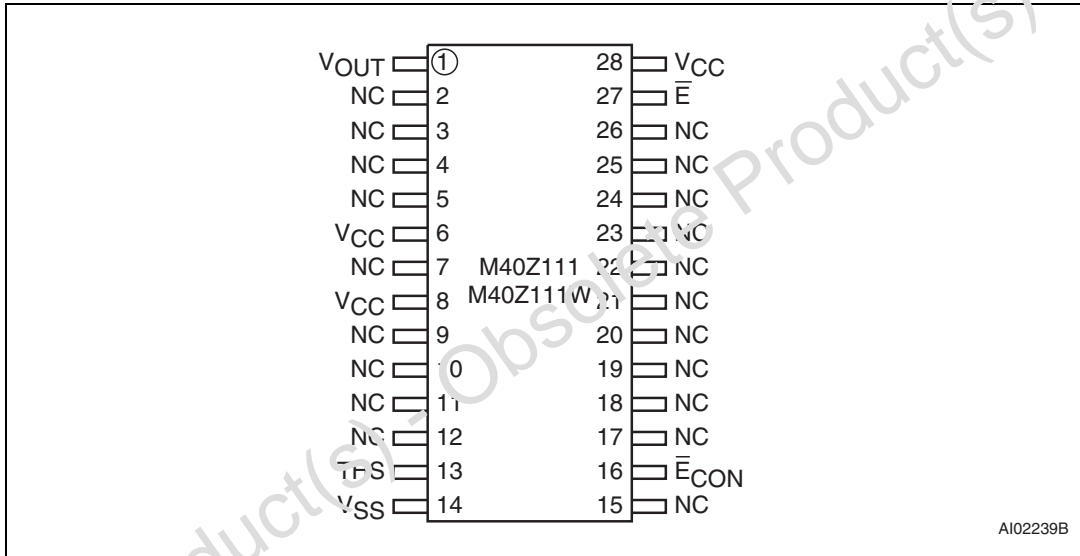
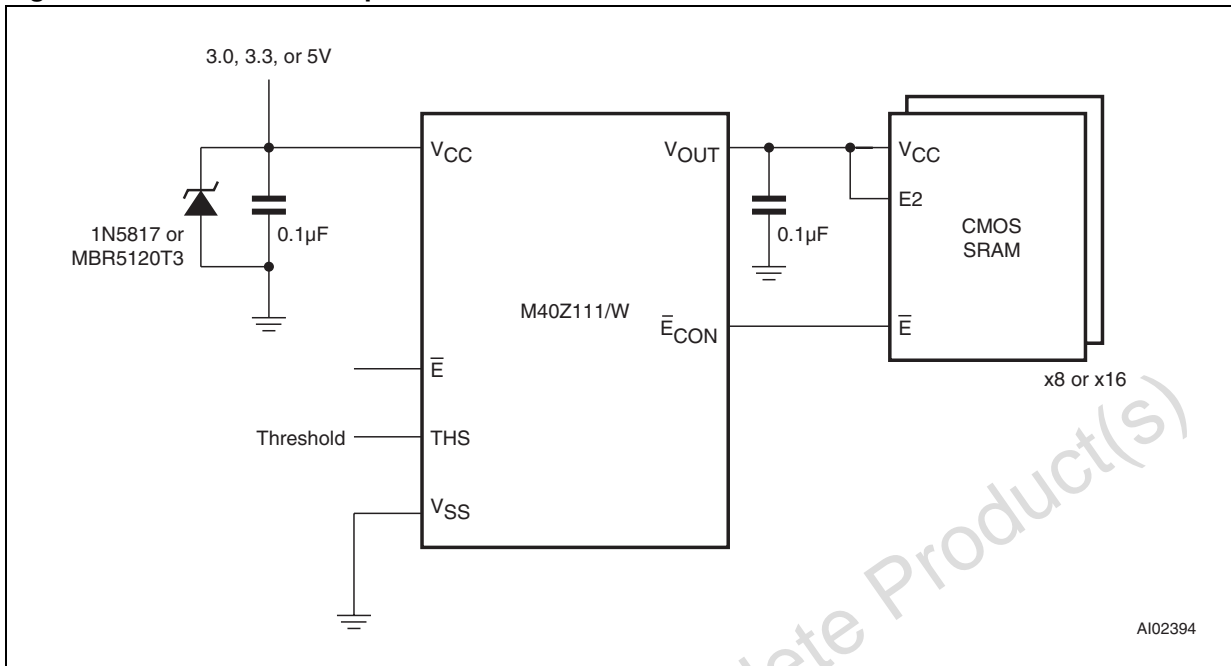


Figure 3. Hardware hookup



Obsolete Product(s) - Obsolete Product(s)

2 Operation

The M40Z111/W, as shown in [Figure 3 on page 7](#), can control up to two standard low-power SRAMs. These SRAMs must be configured to have the chip enable input disable all other input signals. Most slow, low-power SRAMs are configured like this, however many fast SRAMs are not. During normal operating conditions, the conditioned chip enable (\overline{E}_{CON}) output pin follows the chip enable (\overline{E}) input pin with timing shown in [Table 2 on page 10](#). An internal switch connects V_{CC} to V_{OUT} . This switch has a voltage drop of less than 0.3 V (I_{OUT1}).

When V_{CC} degrades during a power failure, \overline{E}_{CON} is forced inactive independent of \overline{E} . In this situation, the SRAM is unconditionally write protected as V_{CC} falls below an out-of-tolerance threshold (V_{PFD}). The power fail detection value associated with V_{PFD} is selected by the THS pin and is shown in [Table 6 on page 13](#).

Note: The THS pin must be connected to either V_{SS} or V_{OUT} .

If chip enable access is in progress during a power fail detection, that memory cycle continues to completion before the memory is write protected. If the memory cycle is not terminated within time t_{WP} , \overline{E}_{CON} is unconditionally driven high, write protecting the SRAM.

A power failure during a write cycle may corrupt data at the currently addressed location, but does not jeopardize the rest of the SRAM's contents. At voltages below V_{PFD} (min), the user can be assured the memory will be write protected provided the V_{CC} fall time exceeds t_F .

As V_{CC} continues to degrade, the internal switch disconnects V_{CC} and connects the internal battery to V_{OUT} . This occurs at the switch over voltage (V_{SO}). Below the V_{SO} , the battery provides a voltage V_{OHB} to the SRAM and can supply current I_{OUT2} (see [Table 6 on page 13](#)). When V_{CC} rises above V_{SO} , V_{OUT} is switched back to the supply voltage. Output \overline{E}_{CON} is held inactive for t_{ER} (200 ms maximum) after the power supply has reached V_{PFD} , independent of the \overline{E} input, to allow for processor stabilization (see [Figure 5 on page 9](#)).

2.1 Data retention lifetime calculation

Most low power SRAMs on the market today can be used with the M40Z111/W NVRAM SUPERVISOR. There are, however some criteria which should be used in making the final choice of which SRAM to use. The SRAM must be designed in a way where the chip enable input disables all other inputs to the SRAM. This allows inputs to the M40Z111/W and SRAMs to be "Don't Care" once V_{CC} falls below V_{PFD} (min). The SRAM should also guarantee data retention down to $V_{CC} = 2.0$ V. The chip enable access time must be sufficient to meet the system needs with the chip enable propagation delays included. If the SRAM includes a second chip enable pin (E2), this pin should be tied to V_{OUT} . If data retention lifetime is a critical parameter for the system, it is important to review the data retention current specifications for the particular SRAMs being evaluated. Most SRAMs specify a data retention current at 3.0 V.

Manufacturers generally specify a typical condition for room temperature along with a worst case condition (generally at elevated temperatures). The system level requirements will determine the choice of which value to use. The data retention current value of the SRAMs can then be added to the I_{CCDR} value of the M40Z111/W to determine the total current requirements for data retention.

The available battery capacity for the SNAPHAT[®] of your choice can then be divided by this current to determine the amount of data retention available (see [Table 11 on page 18](#)). For more information on battery storage life refer to the application note AN1012.

Figure 4. Power-down timing

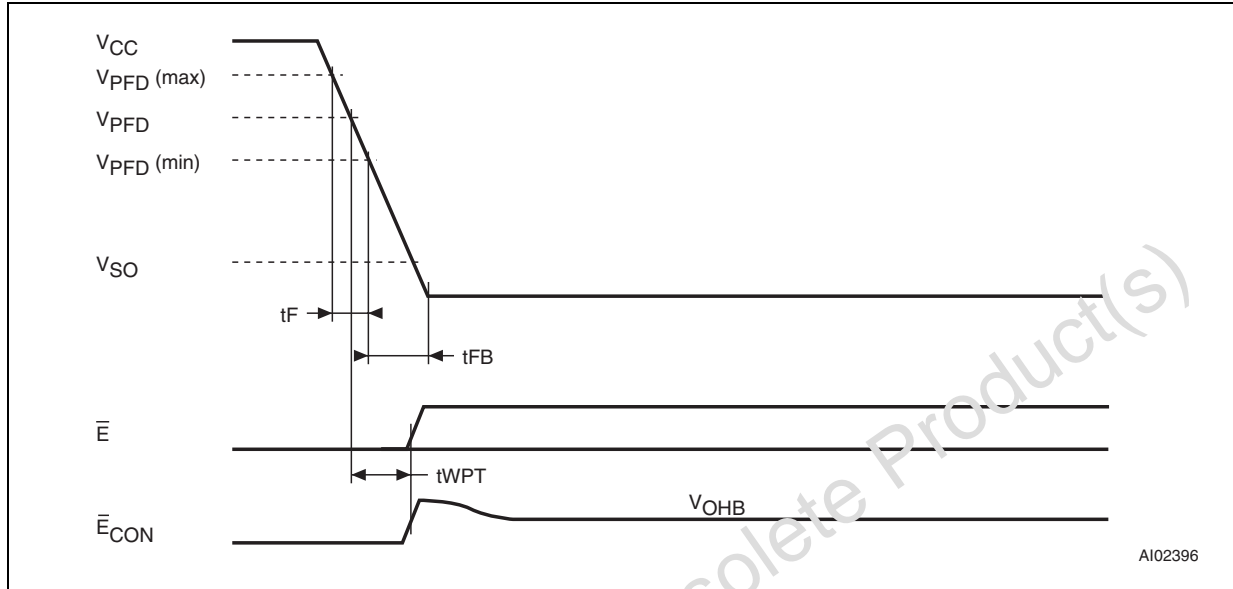


Figure 5. Power-up timing

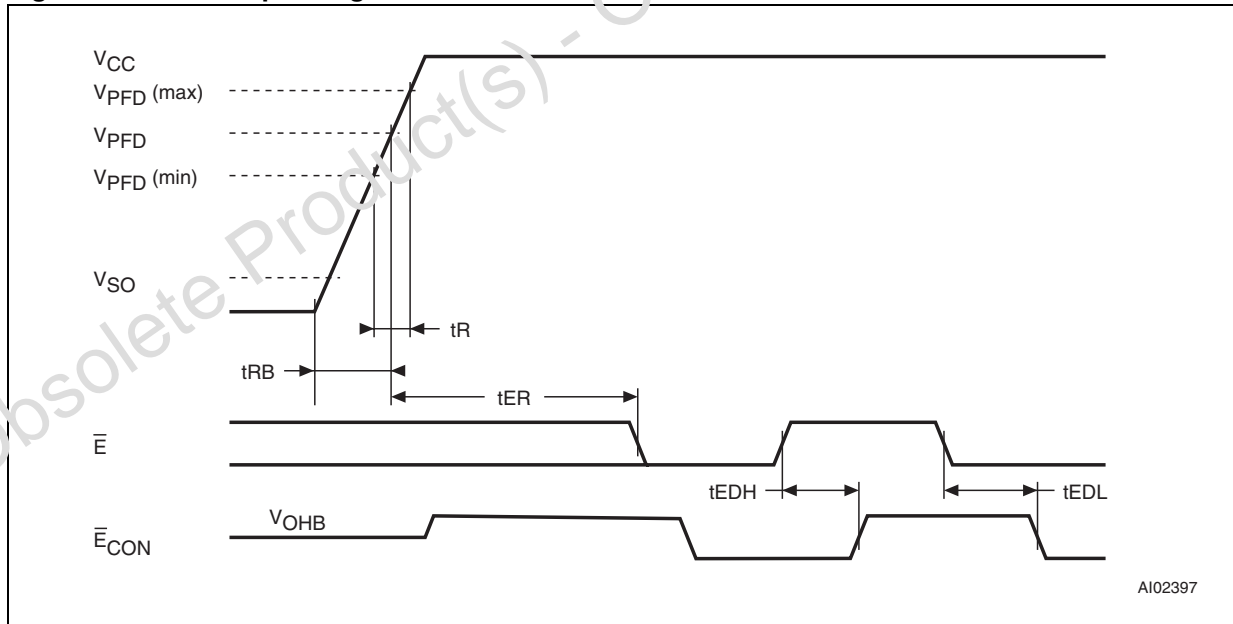


Table 2. Power down/up AC characteristics

| Symbol | Parameter ⁽¹⁾ | Min | Max | Unit | |
|----------------|---|----------|-----|---------|---------|
| $t_F^{(2)}$ | $V_{PFD} (max)$ to $V_{PFD} (min)$ V_{CC} fall time | 300 | | μs | |
| $t_{FB}^{(3)}$ | $V_{PFD} (min)$ to V_{SS} V_{CC} fall time | 10 | | μs | |
| t_R | $V_{PFD} (min)$ to $V_{PFD} (max)$ V_{CC} rise time | 10 | | μs | |
| t_{RB} | V_{SS} to $V_{PFD} (min)$ V_{CC} rise time | 1 | | μs | |
| t_{EDL} | Chip enable propagation delay | M40Z111 | 15 | ns | |
| | | M40Z111W | 20 | ns | |
| t_{EDH} | Chip enable propagation delay | M40Z111 | 10 | ns | |
| | | M40Z111W | 20 | ns | |
| $t_{ER}^{(4)}$ | Chip enable recovery | 40 | 200 | ms | |
| t_{WPT} | Write protect time | M40Z111 | 40 | 150 | μs |
| | | M40Z111W | 40 | 250 | μs |

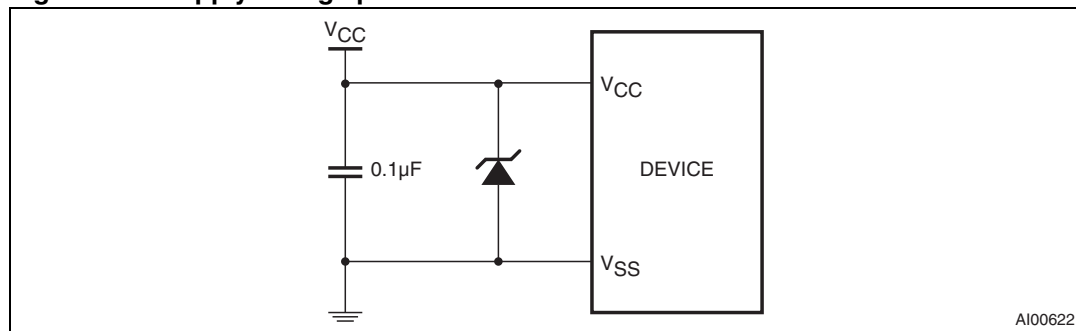
- Valid for ambient operating temperature: $T_A = -40$ to 85 °C; $V_{CC} = 4.5$ to 5.5 V or 2.7 to 3.6 V (except where noted).
- $V_{PFD} (max)$ to $V_{PFD} (min)$ fall time of less than t_F may result in deselection/write protection not occurring until $200 \mu s$ after V_{CC} passes $V_{PFD} (min)$.
- $V_{PFD} (min)$ to V_{SS} fall time of less than t_{FB} may cause corruption of RAM data.
- $t_{ER} (min) = 20$ ms for industrial temperature range - grade 6 device.

2.2 V_{CC} noise and negative going transients

V_{CC} transients, including those produced by output switching, can produce voltage fluctuations, resulting in spikes on the V_{CC} bus. These transients can be reduced if capacitors are used to store energy which stabilizes the V_{CC} bus. The energy stored in the bypass capacitors will be released as low going spikes are generated or energy will be absorbed when overshoots occur. A ceramic bypass capacitor value of $0.1 \mu F$ (as shown in [Figure 6](#)) is recommended in order to provide the needed filtering.

In addition to transients that are caused by normal SRAM operation, power cycling can generate negative voltage spikes on V_{CC} that drive it to values below V_{SS} by as much as one volt. These negative spikes can cause data corruption in the SRAM while in battery backup mode. To protect from these voltage spikes, STMicroelectronics recommends connecting a Schottky diode from V_{CC} to V_{SS} (cathode connected to V_{CC} , anode to V_{SS}). Schottky diode 1N5817 is recommended for through hole and MBR5120T3 is recommended for surface mount.

Figure 6. Supply voltage protection



3 Maximum ratings

Stressing the device above the rating listed in the absolute maximum ratings table may cause permanent damage to the device. These are stress ratings only and operation of the device at these or any other conditions above those indicated in the operating sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

Table 3. Absolute maximum ratings

| Symbol | Parameter | | Value | Unit |
|-----------------|--|----------|------------------------|------|
| T_A | Ambient operating temperature | Grade 6 | -40 to 85 | °C |
| T_{STG} | Storage temperature (V_{CC} off) | SNAPHAT® | -40 to 85 | °C |
| | | SOIC | -55 to 125 | °C |
| $T_{SLD}^{(1)}$ | Lead solder temperature for 10 seconds | | 260 | °C |
| V_{IO} | Input or output voltages | | -0.3 to $V_{CC} + 0.3$ | V |
| V_{CC} | Supply voltage | M40Z111 | -0.3 to 7.0 | V |
| | | M40Z111W | -0.3 to 4.6 | V |
| I_O | Output current | | 20 | mA |
| P_D | Power dissipation | | 1 | W |

1. For SO package, lead-free (Pb-free) lead finish: reflow at peak temperature of 260 °C (the time above 255 °C must not exceed 30 seconds).

Caution: Negative undershoots below -0.3 V are not allowed on any pin while in the battery backup mode.

Caution: Do NOT wave solder SOIC to avoid damaging SNAPHAT sockets.

4 DC and AC parameters

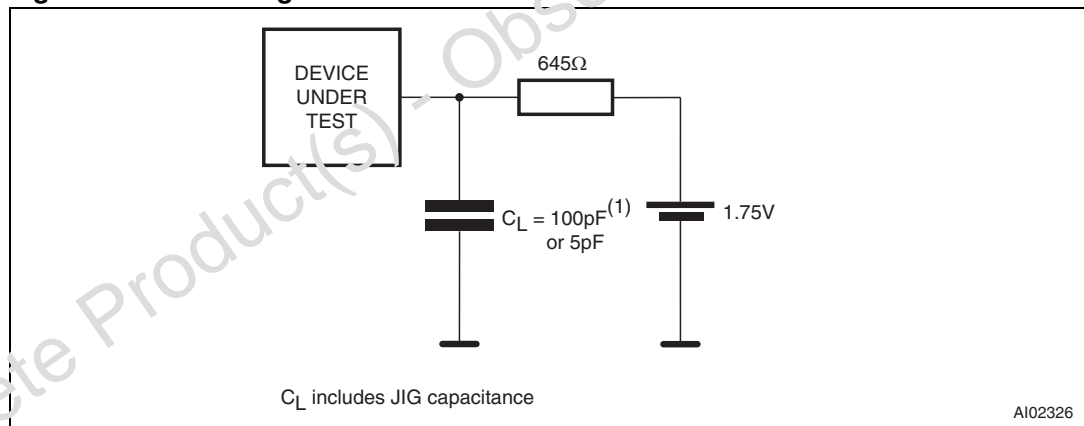
This section summarizes the operating and measurement conditions, as well as the DC and AC characteristics of the device. The parameters in the following DC and AC characteristic tables are derived from tests performed under the measurement conditions listed in [Table 4: DC and AC measurement conditions](#). Designers should check that the operating conditions in their projects match the measurement conditions when using the quoted parameters.

Table 4. DC and AC measurement conditions

| Parameter | M40Z111 | M40Z111W |
|---------------------------------------|--------------|--------------|
| V _{CC} supply voltage | 4.5 to 5.5 V | 2.7 to 3.6 V |
| Ambient operating temperature | -40 to 85 °C | -40 to 85 °C |
| Load capacitance (C _L) | 100 pF | 50 pF |
| Input rise and fall times | ≤ 5 ns | ≤ 5 ns |
| Input pulse voltages | 0 to 3 V | 0 to 3 V |
| Input and output timing ref. voltages | 1.5 V | 1.5 V |

Note: Note that Output Hi-Z is defined as the point where data is no longer driven.

Figure 7. AC testing load circuit



1. 50 pF for M40Z111W.

Table 5. Capacitance

| Symbol | Parameter ⁽¹⁾⁽²⁾ | Min | Max | Unit |
|---------------------------------|-----------------------------|-----|-----|------|
| C _{IN} | Input capacitance | - | 8 | pF |
| C _{OUT} ⁽³⁾ | Output capacitance | - | 10 | pF |

1. Effective capacitance measured with power supply at 5 V (M40Z111) or 3.3 V (M40Z111W); sampled only, not 100% tested.
2. At 25 °C, f = 1 MHz.
3. Outputs deselected

Table 6. DC characteristics

| Sym | Parameter | Test condition ⁽¹⁾ | M40Z111 | | | M40Z111W | | | Unit |
|--------------------------------|---|---|-----------------|------|-----------------------|-----------------|---------------------------|-----------------------|------|
| | | | Min | Typ | Max | Min | Typ | Max | |
| I _{CC} | Supply current | Outputs open | | 3 | 6 | | 2 | 4 | mA |
| I _{CCDR} | Data retention mode current | | | | 150 | | | 150 | nA |
| I _{LI} | Input leakage current | 0 V ≤ V _{IN} ≤ V _{CC} | | | ±1 | | | ±1 | μA |
| I _{LO} ⁽²⁾ | Output leakage current | 0 V ≤ V _{OUT} ≤ V _{CC} | | | ±1 | | | ±1 | μA |
| I _{OUT1} | V _{OUT} current (active) | V _{OUT} > V _{CC} - 0.3 | | | 160 | | | 100 | mA |
| | | V _{OUT} > V _{CC} - 0.2 | | | 100 | | | 65 | mA |
| I _{OUT2} | V _{OUT} current (battery backup) | V _{OUT} > V _{BAT} - 0.3 | | 100 | | | 100 | | μA |
| V _{BAT} | Battery voltage | | 2.0 | 3.0 | 3.5 | 2.0 | 3.0 | 3.5 | V |
| V _{IH} | Input high voltage | | 2.2 | | V _{CC} + 0.3 | 2.0 | | V _{CC} + 0.3 | V |
| V _{IL} | Input low voltage | | -0.3 | | 0.8 | -0.3 | | 0.8 | V |
| V _{OH} | Output high voltage | I _{OH} = -2.0 mA | 2.4 | | | 2.4 | | | V |
| V _{OHb} | V _{OH} battery backup | I _{OUT2} = -1.0 μA | 2.0 | 2.9 | 3.6 | 2.0 | 2.9 | 3.6 | V |
| V _{OL} | Output low voltage | I _{OL} = 4.0 mA | | | 0.4 | | | 0.4 | V |
| THS | Threshold select voltage | | V _{SS} | | V _{OUT} | V _{SS} | | V _{OUT} | V |
| V _{PFD} | Power-fail deselect voltage (THS = V _{SS}) | | 4.50 | 4.60 | 4.75 | 2.80 | 2.90 | 3.00 | V |
| | Power-fail deselect voltage (THS = V _{OUT}) | | 4.20 | 4.35 | 4.50 | 2.50 | 2.60 | 2.70 | V |
| V _{SO} | Battery back-up switchover voltage | | | 3.0 | | | V _{PFD} - 100 mV | | V |

1. Valid for ambient operating temperature: T_A = -40 to 85 °C; V_{CC} = 4.5 to 5.5 V or 2.7 to 3.6 V (except where noted).

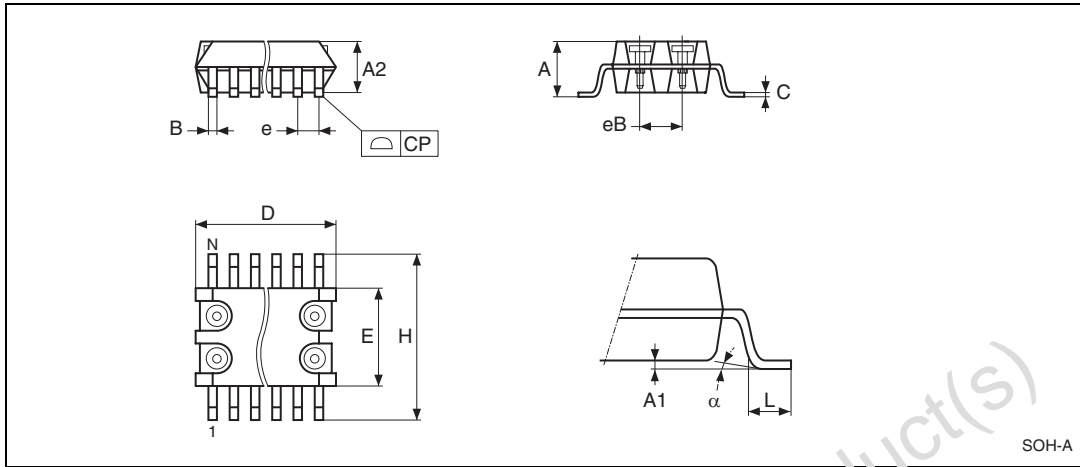
2. Outputs deselected.

5 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

Obsolete Product(s) - Obsolete Product(s)

Figure 8. SOH28 – 28-lead plastic small outline, 4-socket battery SNAPHAT, package outline

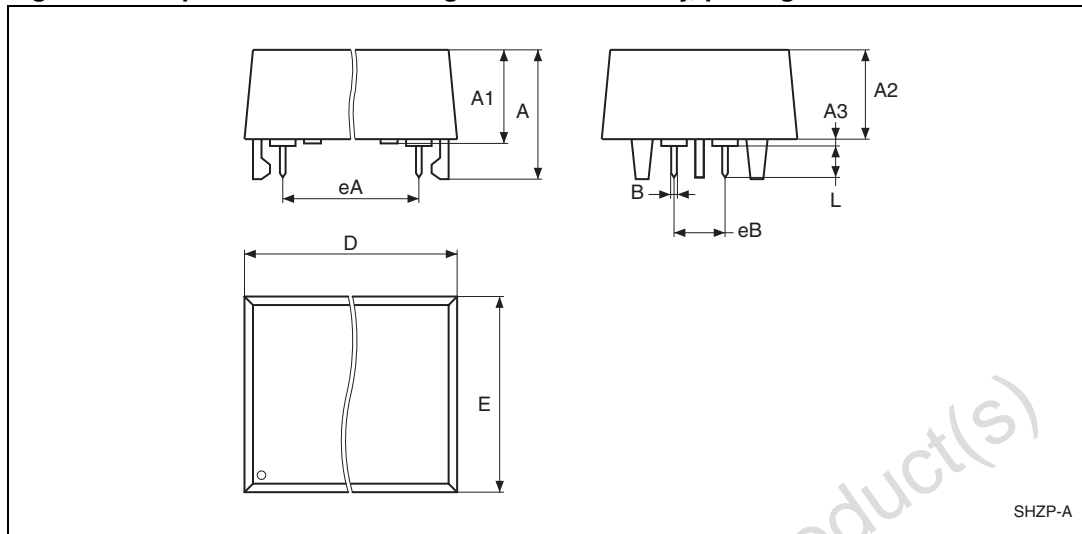


Note: Drawing is not to scale.

Table 7. SOH28 – 28-lead plastic small outline, battery SNAPHAT, pack. mech. data

| Symbol | mm | | | inches | | |
|--------|------|-------|-------|--------|-------|-------|
| | Typ | Min | Max | Typ | Min | Max |
| A | | | 3.05 | | | 0.120 |
| A1 | | 0.05 | 0.36 | | 0.002 | 0.014 |
| A2 | | 2.34 | 2.69 | | 0.092 | 0.106 |
| B | | 0.36 | 0.51 | | 0.014 | 0.020 |
| C | | 0.15 | 0.32 | | 0.006 | 0.012 |
| D | | 17.71 | 18.49 | | 0.697 | 0.728 |
| E | | 8.23 | 8.89 | | 0.324 | 0.350 |
| e | 1.27 | – | – | 0.050 | – | – |
| eB | | 3.20 | 3.61 | | 0.126 | 0.142 |
| H | | 11.51 | 12.70 | | 0.453 | 0.500 |
| L | | 0.41 | 1.27 | | 0.016 | 0.050 |
| a | | 0° | 8° | | 0° | 8° |
| N | | 28 | | | 28 | |
| CP | | | 0.10 | | | 0.004 |

Figure 9. 4-pin SNAPHAT housing for 48 mAh battery, package outline

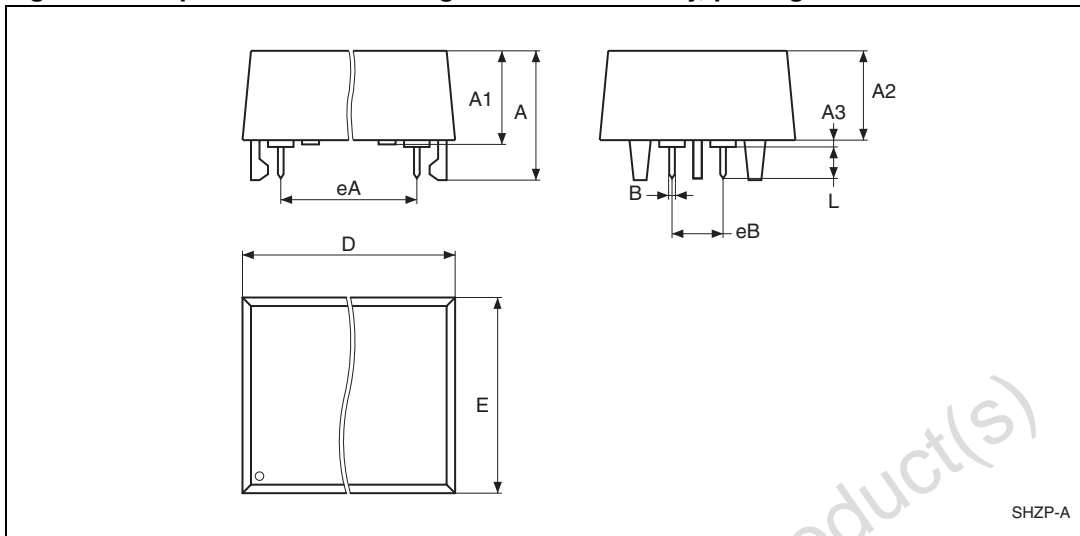


Note: Drawing is not to scale.

Table 8. 4-pin SNAPHAT housing for 48 mAh battery, package mechanical data

| Symbol | mm | | | inches | | |
|--------|-----|-------|-------|--------|-------|-------|
| | Typ | Min | Max | Typ | Min | Max |
| A | | | 9.78 | | | 0.385 |
| A1 | | 6.73 | 7.24 | | 0.265 | 0.285 |
| A2 | | 6.48 | 6.99 | | 0.255 | 0.275 |
| A3 | | | 0.38 | | | 0.015 |
| B | | 0.46 | 0.56 | | 0.018 | 0.022 |
| D | | 21.21 | 21.84 | | 0.835 | 0.860 |
| E | | 14.22 | 14.99 | | 0.560 | 0.590 |
| eA | | 15.55 | 15.95 | | 0.612 | 0.628 |
| eB | | 3.20 | 3.61 | | 0.126 | 0.142 |
| L | | 2.03 | 2.29 | | 0.080 | 0.090 |

Figure 10. 4-pin SNAPHAT housing for 120 mAh battery, package outline



Note: Drawing is not to scale.

Table 9. 4-pin SNAPHAT housing for 120 mAh battery, package mechanical data

| Symbol | mm | | | inches | | |
|--------|-----|-------|-------|--------|-------|-------|
| | Typ | Min | Max | Typ | Min | Max |
| A | | | 10.54 | | | 0.415 |
| A1 | | 8.00 | 8.51 | | 0.315 | 0.335 |
| A2 | | 7.24 | 8.00 | | 0.285 | 0.315 |
| A3 | | | 0.38 | | | 0.015 |
| B | | 0.46 | 0.56 | | 0.018 | 0.022 |
| D | | 21.21 | 21.84 | | 0.835 | 0.860 |
| E | | 17.27 | 18.03 | | 0.680 | 0.710 |
| eA | | 15.55 | 15.95 | | 0.612 | 0.628 |
| eB | | 3.20 | 3.61 | | 0.126 | 0.142 |
| L | | 2.03 | 2.29 | | 0.080 | 0.090 |

6 Part numbering

Table 10. Ordering information scheme

| Example: | M40Z | 111W | MH | 6 | E |
|---|------|--|---------------------------|------------------|--|
| Device type | M40Z | | | | |
| Supply voltage and write protect voltage | | 111 ⁽¹⁾ = $V_{CC} = 4.5 \text{ to } 5.5 \text{ V}$; $V_{PFD} = 4.3 \text{ to } 4.5 \text{ V}$ $THS = V_{SS} = 4.5 \leq V_{PFD} \leq 4.75 \text{ V}$ $THS = V_{OUT} = 4.2 \leq V_{PFD} \leq 4.5 \text{ V}$ 111W ⁽¹⁾ = $V_{CC} = 2.7 \text{ to } 3.6 \text{ V}$; $V_{PFD} = 2.6 \text{ to } 2.7 \text{ V}$ $THS = V_{SS} = 2.8 \leq V_{PFD} \leq 3.0 \text{ V}$ $V_{CC} = 2.7 \text{ to } 3.3 \text{ V}$ $THS = V_{OUT} = 2.5 \leq V_{PFD} \leq 2.7 \text{ V}$ | | | |
| Package | | | MH ⁽²⁾ = SOH28 | | |
| Temperature range | | | | 6 = -40 to 85 °C | |
| Shipping method for SOIC | | | | | E = Lead-free ECOPACK [®] package, tubes F = Lead-free ECOPACK [®] package, tape & reel |

1. Not recommended for new design. Contact local ST sales office for availability.
2. The SOIC package (SOH28) requires the battery package (SNAPHAT[®]) which is ordered separately under the part number "M4ZXX-BR00SHX" in plastic tubes or "M4ZXX-BR00SHXTR" in tape & reel form.

Caution: Do not place the SNAPHAT battery package "M4ZXX-BR00SH" in conductive foam as this will drain the lithium button-cell battery.

For a list of available options (e.g., speed, package) or for further information on any aspect of this device, please contact the ST sales office nearest to you.

Table 11. Battery table

| Part number | Description | Package |
|---------------|-------------------------------------|---------|
| M4Z28-BR00SH1 | SNAPHAT housing for 48 mAh battery | SH |
| M4Z32-BR00SH1 | SNAPHAT housing for 120 mAh battery | SH |

7 Revision history

Table 12. Document revision history

| Date | Revision | Changes |
|-------------|----------|---|
| Sep-2000 | 1 | First Draft Issue |
| 14-Sep-2001 | 2 | Reformatted, TOC added, changed DC Characteristics (Table 6); changed battery, ind. temperature information (Table 3, 2, 10, 11 , Figure 9, 10); Corrected SOIC label (Figure 2); added E2 to Hookup (Figure 3) |
| 13-May-2002 | 3 | Modify reflow time and temperature footnote (Table 3) |
| 12-Nov-2007 | 4 | Reformatted document; added lead-free second level interconnect information to cover page and Section 5: Package mechanical data ; updated Figure 5, Table 3, 10, 11 . |
| 15-Dec-2010 | 5 | Devices are not recommended for new design, updated document status and Table 10 ; updated footnote in Table 3 ; updated ECOPACK® text in Section 5: Package mechanical data ; reformatted document. |

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